L Number	Hits	Search Text	DB	Time stamp
1	0	(silicon or polysilicon) same (pascal or MPa) same (residual adj stress) same (pores or porous or porosity) same (grain or grains)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/05 09:53
2	3	(silicon or polysilicon) same (pascal or MPa) same (residual adj stress) same (pores or porous or porosity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/05 13:19
3	4	("5596219" | "5789753" | "5830372" | "6194722").PN.	USPAT	2004/01/05 10:24
4	23	(silicon or polysilicon) same (grain or grains) same (hemispherical or sperical) same (pores or porous or porosity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/05 13:21
5	0	(silicon or polysilicon) same membrane same (grain or grains) same (hemispherical or sperical) same (pores or porous or porosity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/05 13:51
6	0	(silicon or polysilicon) same membrane same (grain or grains) same (hemispherical or spherical) same (pores or porous or porosity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/05 13:51
7	13	(silicon or polysilicon) same membrane same (grain or grains) same (pores or porous or porosity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/05 14:59
8	3667	((438/1-4) or (438/22-29)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/05 14:59
9	29	(((438/1-4) or (438/22-29)).CCLS.) and (silicon with membrane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/05 14:59
10	0	((((438/1-4) or (438/22-29)).CCLS.) and (silicon with membrane)) and (residual adj stress)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/05 15:00
11	26	(((438/1-4) or (438/22-29)).CCLS.) and (residual adj stress)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/05 15:14
12	0	(((438/1-4) or (438/22-29)).CCLS.) and ((residual adj stress) same (MPa or pascals))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/05 15:16
13	0	(((438/1-4) or (438/22-29)).CCLS.) and ((residual adj stress) same (Pa))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/05 15:16
-	2	semiconductor and substrate and "SiO.sub.2" and "SiN" and (porous same grain$1 same (polysilicon or (polycrystalline with silicon)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 10:40

-	154	semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain$1 same (polysilicon or (polycrystalline with silicon)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/22 13:34
-	0	semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain$1 same monolayer same (polysilicon or (polycrystalline with silicon)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/22 10:42
--	0	semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain$1 same (monomolecular adj layer) same (polysilicon or (polycrystalline with silicon)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/22 10:43
-	5	semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain$1 same (thin adj layer) same (polysilicon or (polycrystalline with silicon)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/22 10:50
--	0	semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain$1 same (membrane) same (polysilicon or (polycrystalline with silicon)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/22 10:50
-	154	semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain$1 same (polysilicon or (polycrystalline with silicon)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/22 13:34
--	28	(semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain$1 same (polysilicon or (polycrystalline with silicon)))) and filter	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/22 13:41
-	0	(semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain$1 same (polysilicon or (polycrystalline with silicon)))) and (sacrificial with layer) and HF	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/22 13:42
-	5	(semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain$1 same (polysilicon or (polycrystalline with silicon)))) and (sacrificial with layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/22 15:45
-	0	semiconductor and (micromachined with encapsulation) and (permeable with polysilicon) and HF	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/22 15:46
-	0	semiconductor and (micromachined with encapsulation) and (polysilicon) and HF	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/22 15:46
-	183	semiconductor and (micromachined) and (polysilicon) and HF	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/22 15:47
--	0	(semiconductor and (micromachined) and (polysilicon) and HF) and SiO and SiN	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/22 15:47
-	24	(semiconductor and (micromachined) and (polysilicon) and HF) and SiN	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/22 15:47

–	22	((semiconductor and (micromachined) and (polysilicon) and HF) and SiN) and oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/22 15:56
–	19	Lebouitz.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/22 15:56
–	8	Lebouitz.in. and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/22 15:57
–	8	(Lebouitz.in. and polysilicon) and oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/22 15:57
–	8	((Lebouitz.in. and polysilicon) and oxide) and nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/22 15:57
–	10	"718010"	USPAT; US-PGPUB	2003/01/23 13:14
–	6	(("5919364") or ("5651900") or ("4801380")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/24 22:32
–	3	(("5919364") or ("5651900") or ("4801380")).PN.	USPAT	2003/01/24 22:32
–	658	(silicon or Si) with (residual with stress)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 13:19
–	54	((silicon or Si) with (residual with stress)) with (Pa or pascals or MPa)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 11:08
–	18	(US-5949570-$ or US-5920418-$ or US-5894452-$ or US-5878105-$ or US-5744378-$ or US-6663973-$ or US-6622373-$ or US-6610815-$ or US-6489066-$ or US-6396900-$ or US-6383317-$ or US-6359276-$ or US-6342333-$ or US-6072620-$).did. or (JP-2002038260-$).did. or (JP-2001214055-$ or JP-06305862-$ or JP-06305861-$).did.	USPAT; JPO; DERWENT	2003/12/31 11:08
–	0	((US-5949570-$ or US-5920418-$ or US-5894452-$ or US-5878105-$ or US-5744378-$ or US-6663973-$ or US-6622373-$ or US-6610815-$ or US-6489066-$ or US-6396900-$ or US-6383317-$ or US-6359276-$ or US-6342333-$ or US-6072620-$).did. or (JP-2002038260-$).did. or (JP-2001214055-$ or JP-06305862-$ or JP-06305861-$).did.) and sacrificia	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 11:08

–	1	((US-5949570-$ or US-5920418-$ or US-5894452-$ or US-5878105-$ or US-5744378-$ or US-6663973-$ or US-6622373-$ or US-6610815-$ or US-6489066-$ or US-6396900-$ or US-6383317-$ or US-6359276-$ or US-6342333-$ or US-6072620-$).did. or (JP-2002038260-$).did. or (JP-2001214055-$ or JP-06305862-$ or JP-06305861-$).did.) and sacrificial	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 11:09
–	64	((silicon or Si) with (residual with stress)) and sacrificial	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 11:09
–	9	(((silicon or Si) with (residual with stress)) and sacrificial) and filter	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 11:09
–	1	((silicon or Si) with (residual with stress)) and (grain with pores with membrane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 13:20
–	1	((silicon or Si) with (residual with stress)) and (grain with pore$1 with membrane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 13:20
–	1	((silicon or Si) with (residual with stress)) and (grain with pore$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 13:20
–	2	((silicon or Si) with (residual with stress)) and (grain$1 with pore$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 13:21
–	7	((silicon or Si) with (residual with stress)) and (membrane with pore$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 13:27
–	2	((silicon or Si) with (residual with stress)) and (membrane with porosity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 13:37
–	3	("6146543").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 13:55
–	12	("4399424" | "4740410" | "4897360" | "4966646" | "5068203" | "5177579" | "5178015" | "5348617" | "5622633" | "5627396" | "5725729" | "5804462").PN.	USPAT	2003/12/31 13:37
–	14	5622633.URPN.	USPAT	2003/12/31 13:45
–	73	4740410.URPN.	USPAT	2003/12/31 13:46
–	4808	((438/764) or (438/767) or (438/694) or (210/321.84) or (210/500.25) or (210/500.26) or (156/625.1)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 13:56

-	255	((((438/764) or (438/767) or (438/694) or (210/321.84) or (210/500.25) or (210/500.26) or (156/625.1)).CCLS.) and @PD>20030122	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 13:57
-	0	((((438/764) or (438/767) or (438/694) or (210/321.84) or (210/500.25) or (210/500.26) or (156/625.1)).CCLS.) and @PD>20030122) and (residual with stress)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 13:57
-	11	((((438/764) or (438/767) or (438/694) or (210/321.84) or (210/500.25) or (210/500.26) or (156/625.1)).CCLS.) and (residual with stress)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 14:09
-	4337	(((427/2.3) or (427/167) or (427/255.27) or (427/452) or (427/563) or (427/567) or (427/574) or (427/578) or (427/588) or (438/647) or (438/657) or (438/684) or (438/719) or (438/753)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 14:10
-	29	(((427/2.3) or (427/167) or (427/255.27) or (427/452) or (427/563) or (427/567) or (427/574) or (427/578) or (427/588) or (438/647) or (438/657) or (438/684) or (438/719) or (438/753)).CCLS.) and (residual with stress)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 14:41